

# MICROCOMPUTER and PERIPHERAL LSI's

## MOS LSI Memories

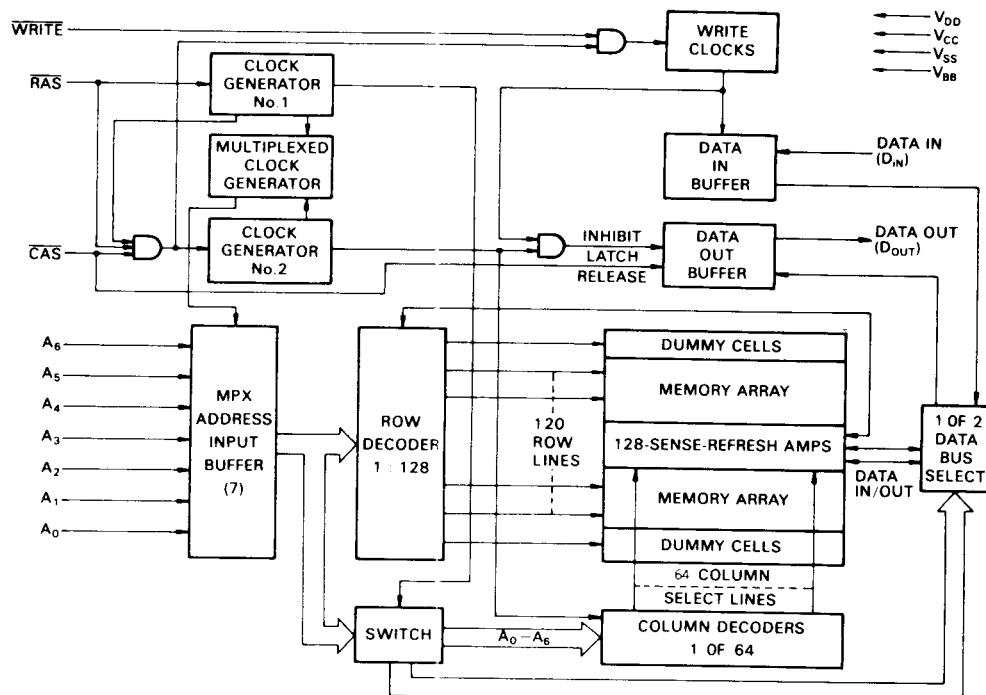
Type No.	Function	Maximum Ratings (Ta=25°C)	Electrical Characteristics (Ta=25°C)							
			Item	Symbol	Condition	min.	typ.	max.	Unit	
MN4116	16,384×1-Bit Dynamic RAM	$V_{TE} = -0.5 \sim +20V$ $V_{DD} = -1.0 \sim +15V$ $V_{CC} = -1.0 \sim +15V$ $V_{BB} - V_{SS} = 0V$ $T_{opr} = 0 \sim +70^\circ C$ $T_{stg} = -65 \sim +150^\circ C$  $V_{DD} = +12V$ $V_{CC} = +5V$ $V_{BB} = -5V$ $V_{SS} = 0V$ $Ta = 25^\circ C$	Supply Current	$I_{DD1}$				35	mA	
				$I_{CC2}$				1.5	mA	
			Total Power Consumption	$P_{tot}$	Operation			462	mW	
				$P_{tot}$	Standby			20	mW	
			"H" Level Input Voltage	$V_{IH}$		2.4		7.0	V	
			"L" Level Input Voltage	$V_{IL}$		-1.0		0.8	V	
			Operating Condition	"H" Level Output Voltage	$V_{OH}$	$I_O = -5mA$	2.4		V	
				"L" Level Output Voltage	$V_{OL}$	$I_O = 4.2mA$		0.4	V	
			Access Time	$t_{AC}$				250	ns	
MN5101	256×4-Bit CMOS Static RAM	$V_{TE} = -0.3 \sim V_{DD} + 0.3V$ $P_D = 1W$ $T_{opr} = -10 \sim +80^\circ C$ $T_{stg} = -65 \sim +150^\circ C$  $V_{CC} = +5V$ $V_{SS} = 0V$ $Ta = 25^\circ C$	Supply Current	$I_{CC1}$	$V_i = V_{CC}$ , Operation		5	15	mA	
				$I_{CC2}$	$V_i = 2.2V$ Operation		15	30	mA	
				$I_{CC3}$	$CE_2 \leq 0.2V$ Standby			200	$\mu A$	
			"H" Level Input Voltage	$V_{IH}$		2.2		$V_{CC}$	V	
			"L" Level Input Voltage	$V_{IL}$		-0.3		0.65	V	
			Operating Condition	"H" Level Output Voltage	$V_{OH}$	$I_{OH} = -1mA$	2.4		V	
				"L" Level Output Current	$V_{OL}$	$I_{OL} = 2mA$		0.4	V	
			Input Capacitance	Input Capacitance	$C_I$	$V_i = 0V$		4	8	pF
				Output Capacitance	$C_O$	$V_o = 0V$		8	12	pF
				Access Time	$t_{AC}$				800	ns

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Block Diagram

MN4116 (Package L-13, 16-Lead Plastic DIL)



MN5101 (Package L-17, 22-Lead Plastic DIL)

